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(54) **Multi-layer ceramic package for semiconductor chip**

(57) In a multi-layer ceramic package wherein a plurality of ceramic laminates each has a conductive pattern, and wherein there is an internal cavity of the package within which is bonded a chip or a plurality of chips interconnected to form a chip array, the chip or chip array (16) is connected through short wire bonds (42) at varying laminate levels each having metalized conductive patterns thereon, and the conductive patterns on the respective laminate layers are interconnected either by tunnel openings (32) filled with metalized material, or by edge formed metalizations (34) so that the conductive patterns ultimately connect to a number of pads at the undersurface of the ceramic package when mounted on

to a metalized board. There is achieved a high component density, but because the connecting wire leads are "staggered" or connected at alternating points at package levels, it is possible to maintain a 10 mil spacing and 10 mil size of the wire bond lands.

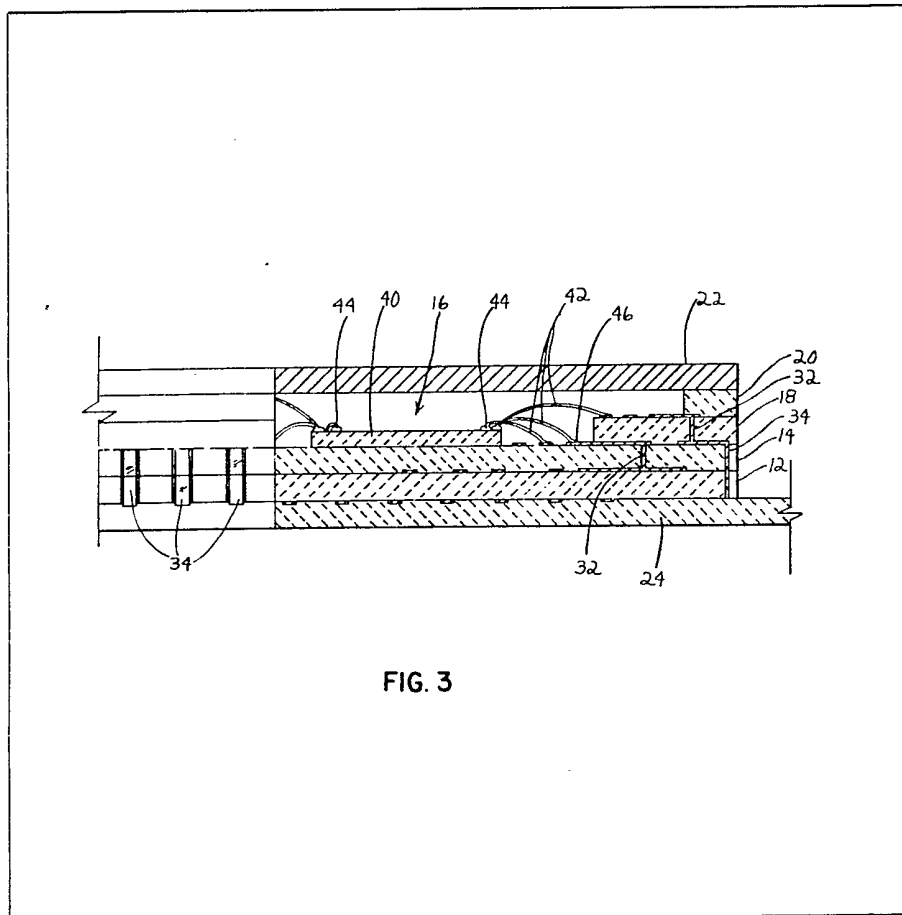


FIG. 3

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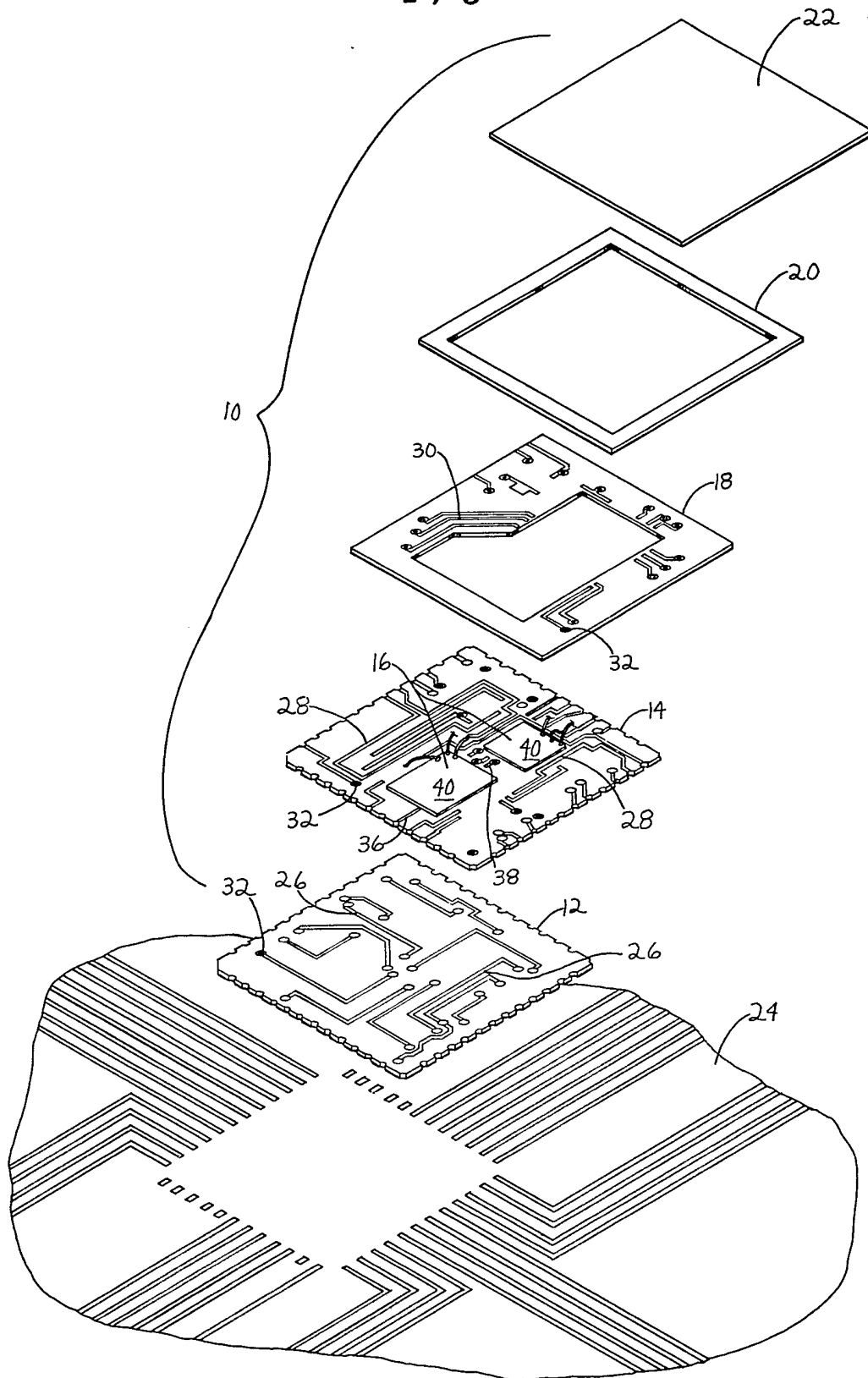


FIG. 1

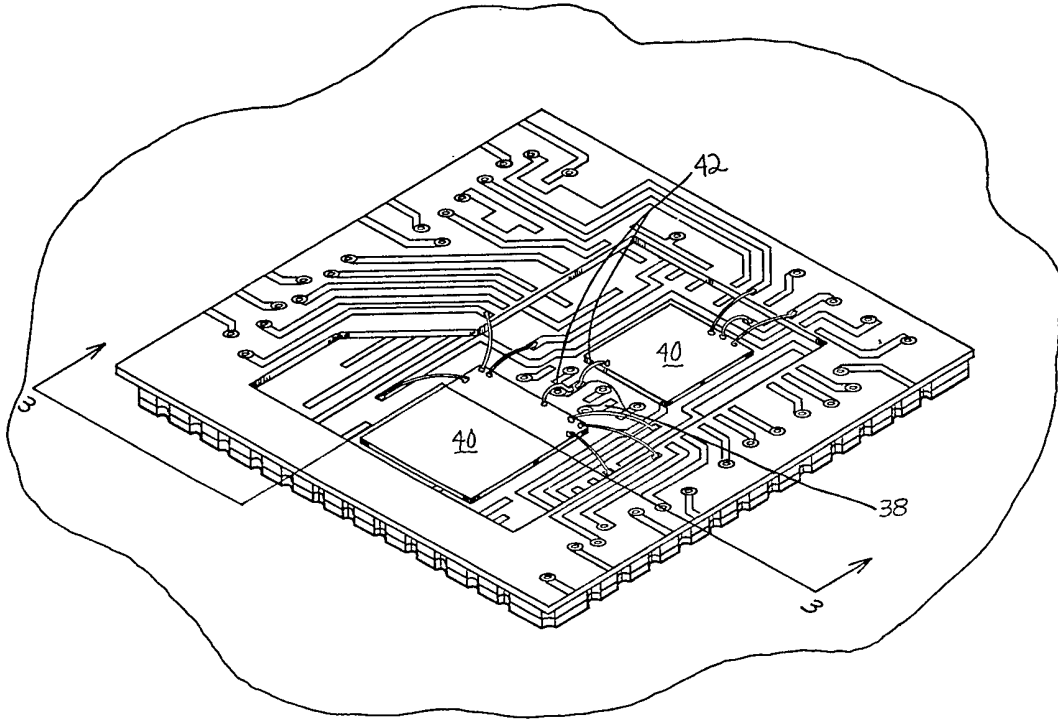


FIG. 2

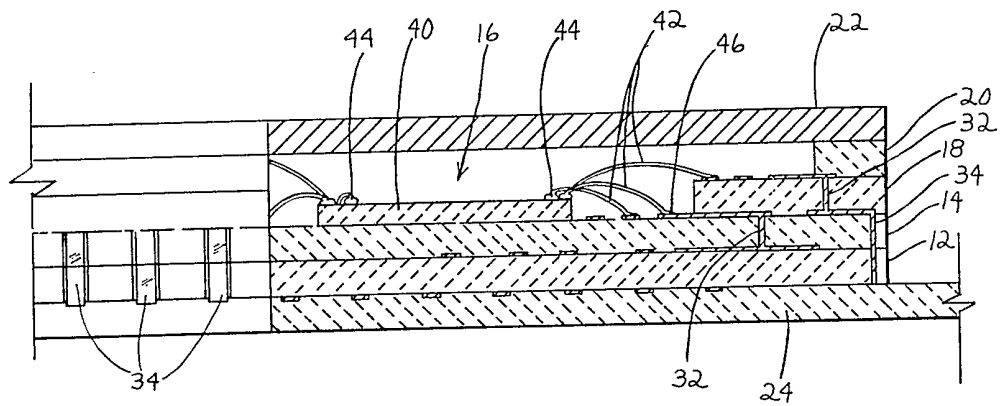


FIG. 3

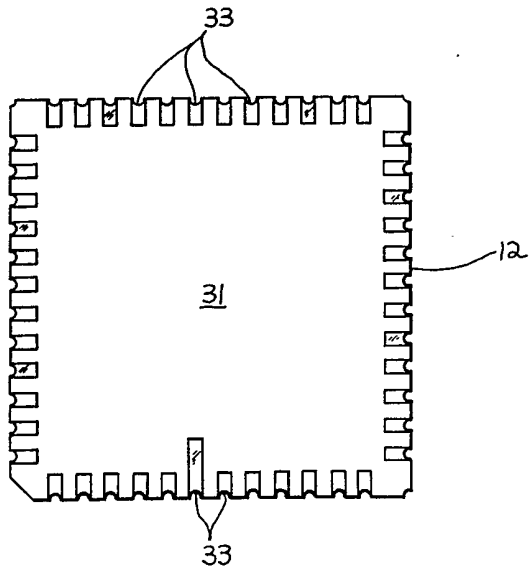


FIG. 4

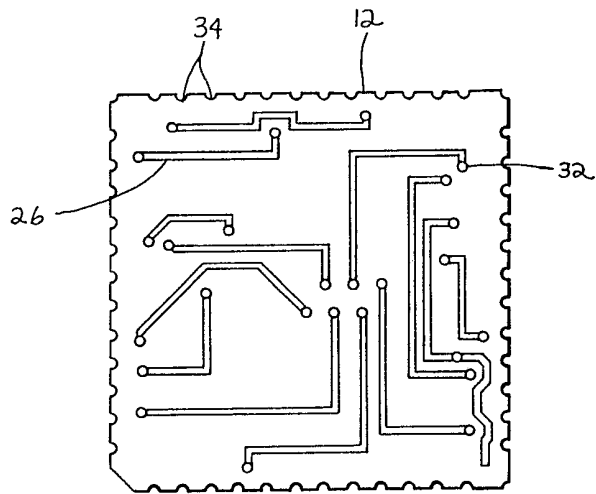


FIG. 4a

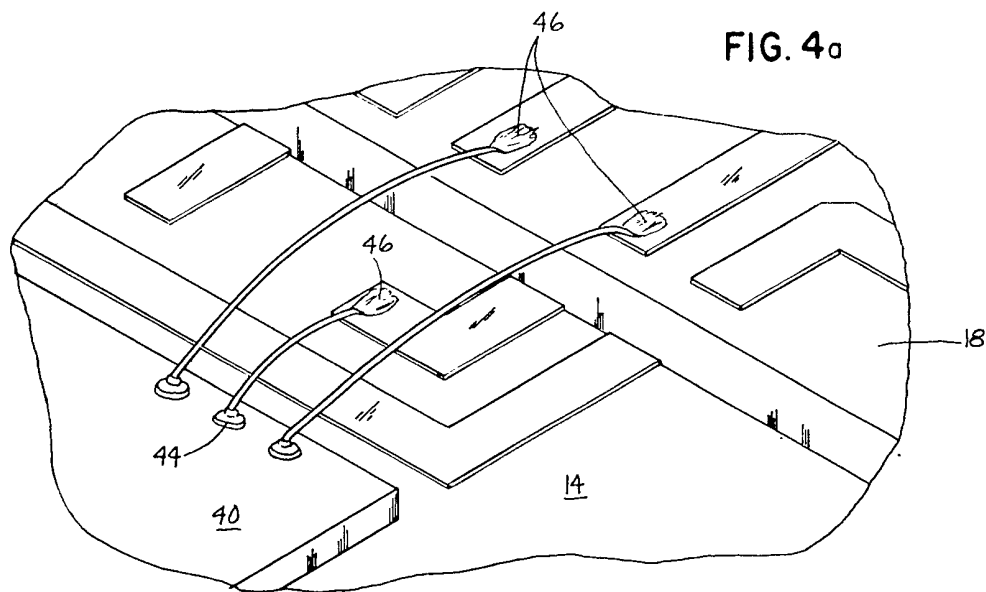


FIG. 5

SPECIFICATION

Multi-layer ceramic package

5 In the packaging of interconnected chip or chip arrays, wire bondings from the chip or chip array, particularly where there is a high component density, or where bonding pads on chips are closely spaced, are excessively crowded, so that there is a real danger that the wire bonds will come into too close proximity with each other and present a serious difficulty in maintaining required spacing for the wires and the bonding lands. This is because the conductive patterns converge upon the chips from the printed metalized patterns provided on the single ceramic laminate. The result is overcrowding of the wire conductors or bondings. However, the trend in multiple circuit chip structures is toward even greater component density, and the conductive patterns on the ceramic package must nevertheless be wire bonded to the chips of the array.

25 Thus, the technology trend, headed as it is toward even greater component density, presents serious and thus far unsolved problems of how to achieve the necessary pin outs, from LSI arrays through wire bondings to the metalized conductive patterns, while still maintaining an industry imposed standard of 10 mil spacings for the pin out wire bonds.

It is an object of the invention to provide a solution to this problem.

35 In accordance with one aspect of the present invention, there is provided a high component density, multi-layer chip carrier in which wire bonds are connected to a single chip or to chips interconnected in a chip array, with the wire bondings then disposed for pin-outs at alternately different layers in the ceramic package, thus achieving greater clearance for the respective wire bonds and wire bonding lands.

45 The present invention makes it possible to increase the density of an interconnected LSI chip array while at the same time providing the necessary pin outputs for wire bondings leading to such array and while maintaining the requisite 10 mil spacing and 10 mil width of metalized wire bonding lands.

In accordance with a further feature of the invention, there is provided an interconnected chip array disposed within a cavity of a multi-layer ceramic package, in which the wire bonds are successively secured between the chip array at one end and to different levels of a multi-layer ceramic package at the other end. The respective levels of the ceramic package are individually metalized for a particular conductive pattern, and the patterns are connected through either or both of metalized connections in the form of "tunneled through" openings from one layer to the other edge metalizations so that the respective con-

ductive patterns are connected, leading ultimately to a series of pads at the undersurface of the ceramic package.

70 Generally, therefore, the present invention provides a multi-layer ceramic package having various level laminates each with a particular conductive pattern, the patterns on the respective layers being connected by either tunneled through or edge metalization bonding, or both. Various pin outs from a central disposed interconnected chip array, disposed within a cavity are connected through wire bonds with said patterns while maintaining an appropriate spacing one relative to the other.

80 According to another aspect of the present invention, there is provided a method for producing a high component density multi-layer chip carrier, comprising the steps of forming a first chip carrier layer adapted to receive at least one chip thereon, and at least one additional layer, forming pin-out conductive connections with said chip, forming metalized conductor paths on said respective layers, and forming wire connections from said chip alternating between staggered paths respectively formed on the differing levels of said layers.

90 Further features of the present invention will become apparent from a consideration of the following description which proceeds with reference to the accompanying drawings in which selected example embodiments are illustrated by way of example and not by way of limitation.

100 In the accompanying drawings:—

Figure 1 is an isometric exploded view illustrating a multi-layer ceramic package, with a printed circuit board at the lower portion and a combination ring and cover at the upper portion which seals an internal cavity in the ceramic package for receiving a chip array;

Figure 2 is an isometric detail view of a multi-layer ceramic package with the ring and cover removed;

Figure 3 is a cross sectional view taken on line 3—3 of Fig. 2 showing the metalized edges, tunnels, and wire bond-pattern connections between the chip array and the various levels of the multi-layer ceramic package;

Figure 4 is the undersurface of the base layer of the ceramic package to be mounted to the metalized board;

Figure 4A is the upper surface of the base layer of the ceramic package and is the opposite face to that of Fig. 4; and

Figure 5 is an enlarged detail view of the ball bond and wedge leads of the wire between the chip array at one wire end and a respective layer of the ceramic package at the other wire end.

Referring to Fig. 1, a multi-layer ceramic package designated generally by reference numeral 10 includes multi-layers of ceramic substrate including a base layer 12, intermediate

layer 14 on which is mounted an interconnected chip array 16, an upper frame layer 18, a ring layer 20, and a cover layer 22. The multi-layer ceramic package as a whole is mounted on a metalized board 24.

The base layer 12, intermediate layer 14, and frame layer 18 each has a printed conductive pattern illustrated by reference numeral 26 in the base layer 12, by reference numeral 28 in the intermediate layer, and by reference numeral 30 for the frame layer 18. The particular pattern of these conductive metalization paths is not a part of the present invention. However, it is contemplated that, prior to assembly, the "green" or unfused ceramic substrates have formed thereon the conductive patterns which are then matched together and electrically connected through connections leading ultimately to pads 33 on the undersurface 31 (Fig. 4) of the base layer 12 for the metalized board 24.

The conductive patterns are communicated one layer with the next, in one instance through "tunnels" 32 (Fig. 3) which are in the form of vertical through openings filled with metalization, and which connect the conductive patterns of one layer to the next. In another instance the conductive patterns of the respective laminates are connected through edge metalizations 34 (Fig. 3).

The interconnected chip array 16 consists of component LSI chips which are connected together. The chips are connected by metalization printed circuits constructed on the confronting surface of intermediate layer 14, and indicated by reference numeral 36.

Between the chips, and to obviate the necessity for the wire bondings to be connected from a chip first outwardly to the periphery of the package and then back to another chip, there can be chip-to-chip wire bonding through lands 38 disposed between and separating the chips 40. These wire bonds are designated generally by reference numeral 42. There is thus provided the interconnections necessary to form a high density interconnected chip array which has pin out connections to the conductive patterns at the respective laminations of the multi-layer ceramic package.

With the high component density described, it is difficult to maintain the 10 mil spacing which is required for conductive patterns. This is achieved, in accordance with a feature of the present invention, in the manner illustrated in Figs. 2 and 3. As shown in these figures, the wire bonds converge upon the chip array connected at one end through a ball bond 44 (Fig. 5) to a chip 40 and at the other end through a wedge bond 46 to a conductive pattern on one or the other of the intermediate layer 14 or frame layer 18. In spite of the high density of LSI chip components and wire bonds, the 10 mil spacing of the conductive patterns is maintained by alter-

nating between layers 14 and 18.

Obviously, there can be more than two alternating layers; three, four or even more layers for alternate wire bonding are contemplated. However, the basic concept, generally, is that by coupling the wire bonds between the centrally disposed high density chip array, and alternately differing levels of the metalized layers, it is possible to increase the number of wire bonds and thus achieve the desired centrally disposed component density while in no way compromising the necessary 10 mil spacing for the conductive patterns.

With regard to manufacture, the wire bonds between the central array and the conductive patterns at the various levels make appropriate connections from layer-to-layer as described, either through tunnels 32 or edge metalizations 34 (Figs. 3 and 4a) all of which ultimately lead to the base layer 12 and underlying pads 33 which are then bonded to appropriate locations on the underlying metalized board 24. The laminants may typically consist of aluminum silicate or other inert substrate materials, which, as stated previously, are green at the time the metalizations, tunnel and edge metalizations are formed thereon.

The layers having a conductive pattern, the ring 20, and the chip array, once the chip array is fixed and wire bondings made with the centrally disposed array, are surmounted with cover layer 22. The package as a whole is next fired (sealed) and the final product mounted on to the metalized board 24.

The chip array is mounted on the intermediate layer 14, and the chips 40 of the array are communicated chip-to-chip through lands 38 on the upper face of the intermediate layer 14, and other layers as required.

The chip array has wire bond connections 42 to the metalized ceramic conductor patterns, made by bonding the ends of the wire bonds so that adjacent wire bonds are connected from the chip array to alternating levels in the multi-layer ceramic package.

The package as a whole is next mounted on the metalized board 24 so that the pads 33 at the exterior surface of the package are mounted on various terminals of the metalized board having a predetermined printed circuit architecture and componentry.

It should be understood that any required conductive pattern can be screened on to the surface of the respective layers of the multi-layer ceramic package, and the conductive pattern as such, i.e. the particular architecture or pattern per se, for example as illustrated, does not form a part of the present invention.

It should be further emphasized that the 10 mil spacing is achievable in the present invention by reason of connecting first one wire from the chip array to a first level and then alternating the wire bonds to a second level, a third level, a fourth level, etc., thereby provid-

ing the means for maintaining a 10 mil of
 conductive patterns spacing in spite of the
 increased component density and the central
 converging of such wires. Quite obviously, if
 5 the 10 mil spacing is not maintained as an
 industry standard, it is equally possible to
 obtain an even higher component density with
 either an agreed upon less than 10 mil spac-
 ing and/or less than 10 mil bonding lands.

10 In all events, the present invention provides
 the possibility of maximum component den-
 sity while maintaining a 10 mil spacing, but is
 equally applicable to whatever component
 density is desired, while achieving an inher-
 15 ently greater density for the respective wire
 bonds.

Although the present invention has been
 illustrated and described in connection with a
 single example embodiment, it will be under-
 20 stood that this is illustrative of the invention
 and is by no means restrictive thereof. For
 example, instead of three ceramic layers of
 the multi-layer ceramic package, it is possible
 to use four, five, or any number desired to
 25 achieve the desired combination of wire spac-
 ing, multi-layering, and various arrangements
 for the printed circuit network as well as the
 architecture of interconnected chip array. All
 of these changes are contemplated as part of
 30 the present invention and it is intended that
 such variations shall be included within the
 scope of the invention as defined by the
 following claims.

35 CLAIMS

1. A method for producing a high compo-
 nent density multi-layer chip carrier, compris-
 ing the steps of forming a first chip carrier
 layer adapted to receive at least one chip
 40 thereon, and at least one additional layer,
 forming pin-out conductive connections with
 said chip, forming metalized conductor paths
 on said respective layers, and forming wire
 connections from said chip alternating be-
 45 tween staggered paths respectively formed on
 the different levels of said layers.

2. The method in accordance with claim
 1, including the steps of forming said multi-
 layers of individually compacted ceramic parti-
 50 cles, and simultaneously firing said compacted
 ceramic layers to sinter the particles and to
 bond the respective layers together.

3. The method in accordance with claim 1
 or claim 2, including the step of disposing a
 55 ring and cover at the upper end of said multi-
 layers, and providing a plurality of pads at the
 outer face of said multi-layer carrier and
 adapted to serve as outlets on a metalized
 board.

4. The method in accordance with claim 1
 or claim 2 or claim 3, including the steps of
 forming a plurality of lands on the layer
 adapted for receiving chips and effecting short
 65 wire bonding between respective chips
 through said lands.

5. The method in accordance with any of
 claims 1 to 4, including the step of sealing an
 interior cavity of said carrier which receives
 said chip and wherein said chip is mounted.

6. The method in accordance with any of
 70 claims 1 to 5, including the step of disposing
 said wire connections between the chip and
 the metalized paths of said layers in alternat-
 ing multi-level connections between said chip
 75 and layers to not less than two alternating
 layers of said multi-layer chip carrier.

7. A multi-layer ceramic package, compris-
 ing a plurality of spaced apart laminants in-
 cluding an intermediate level laminant
 80 adapted to receive a chip array, at least one
 chip disposed on said intermediate level lami-
 nant, conductive patterns on respective ones
 of said laminants, selected ones of said con-
 ductive patterns having wire bonds, metalized
 85 conductive means interconnecting the conduc-
 tive patterns on the respective multi-layered
 laminants, and wire connections maintaining
 not less than a predetermined spacing of said
 wire bonds respectively by extending between
 90 said chip at one end and to alternating levels
 of laminants at the other end to provide
 electrical connections from the chip to said
 conductive patterns.

8. A multi-layer ceramic package in accor-
 95 dence with claim 7, wherein said predeter-
 mined spacing is 10 mil.

9. The multi-layer ceramic package in ac-
 cordance with claim 7 or claim 8, wherein the
 conductive means comprises metalized-filled
 100 openings forming conductive paths between
 the conductive patterns on respective sides of
 selective ones of the laminants forming the
 ceramic package, and edge-formed metalized
 conductive paths interconnecting the conduc-
 105 tive patterns on other of the multi-layer ce-
 ramic laminants, whereby composite conduc-
 tive patterns of said laminants are connected
 together and to said chip.

10. The multi-layer ceramic package in
 110 accordance with any of claims 7 to 9, includ-
 ing means forming lands at the level of the
 ceramic package wherein a chip array is dis-
 posed, and short wire bond connections to the
 land providing a conductor network between
 115 the chips of the chip array, said multi-layer
 ceramic package being adapted for high com-
 ponent density.

11. The multi-layer ceramic package in
 accordance with any of claims 7 to 10, in-
 120 cluding means forming an internal cavity of
 said package, the intermediate level laminant
 includes internal cavity lands for electrically
 inter-connecting the chip.

12. The multi-layer ceramic package in
 125 accordance with any of claims 7 to 11,
 wherein said laminants are formed as com-
 pacted ceramic particle layers, and subse-
 quently fired to develop bonded inter-layer
 connections between confronting surfaces of
 130 the respective ceramic laminants.

13. The multi-layer ceramic package in accordance with any of claims 7 to 12, including a high component density chip array, an internal cavity for receiving said high component density chip array, means forming an interconnected relation of said chips and wire bonds from said interconnected chip array to alternating levels of conductive patterns on the respective multi-level ceramic laminants to form a multi-layer ceramic framing for said multi-layer ceramic package.

14. A method of producing a multi-layer chip carrier substantially as hereinbefore described with reference to the accompanying drawings.

15. A multi-layer ceramic package substantially as hereinbefore described with reference to the accompanying drawings.